

P-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

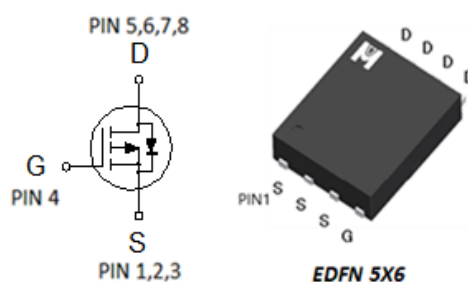
BV _{DSS}	-30V
R _{DS(on)} (MAX.) @V _{GS} =-10V	9.5mΩ
R _{DS(on)} (MAX.) @V _{GS} =-4.5V	17mΩ
I _D @T _C =25°C	-59A

Single P Channel MOSFET

UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)



PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V _{GS}	±25	V
Continuous Drain Current	T _C = 25 °C	I _D	-59	A
	T _A = 25 °C(t ≤ 10s)		-20	
	T _A = 25 °C(Steady-State)		-13	
	T _C = 100 °C		-37	
Pulsed Drain Current ¹		I _{DM}	-184	
Avalanche Current		I _{AS}	-53	
Avalanche Energy	L = 0.1mH	E _{AS}	140	mJ
Power Dissipation	T _C = 25 °C	P _D	50	W
	T _C = 100 °C		20	
Operating Junction & Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C

100% UIS testing in condition of V_D=-15V, L=0.1mH, V_G=-10V, I_L=-15A, Rated V_{DS}=-30V P-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	R _{θJC}		2.5	°C / W
Junction-to-Ambient ³	R _{θJA}		50	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

³50°C / W when mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.5	-3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
		$V_{DS} = 0V, V_{GS} = \pm 25V$			± 500	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
		$V_{DS} = -20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			-10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = -5V, V_{GS} = -10V$	-59			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -25A$		8.5	9.5	m Ω
		$V_{GS} = -4.5V, I_D = -10A$		13.5	17	
Forward Transconductance ¹	g_{fs}	$V_{DS} = -5V, I_D = -25A$		24		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -15V, f = 1MHz$		3067		pF
Output Capacitance	C_{oss}			453		
Reverse Transfer Capacitance	C_{rss}			398		
Gate Resistance	R_g	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		3.0		Ω
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = -15V, V_{GS} = -10V,$ $I_D = -25A$		52		nC
Gate-Source Charge ^{1,2}	Q_{gs}			6.5		
Gate-Drain Charge ^{1,2}	Q_{gd}			10		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = -15V,$ $I_D = -1A, V_{GS} = -10V, R_{GS} = 2.7\Omega$		20		nS
Rise Time ^{1,2}	t_r			18		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			55		
Fall Time ^{1,2}	t_f			10		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Continuous Current	I_S				-59	A
Pulsed Current ³	I_{SM}				-184	
Forward Voltage ¹	V_{SD}	$I_F = -24A, V_{GS} = 0V$			-1.2	V
Reverse Recovery Time	t_{rr}	$I_F = I_S, dI_F/dt = 100A / \mu S$		47		nS
Reverse Recovery Charge	Q_{rr}			43		nC

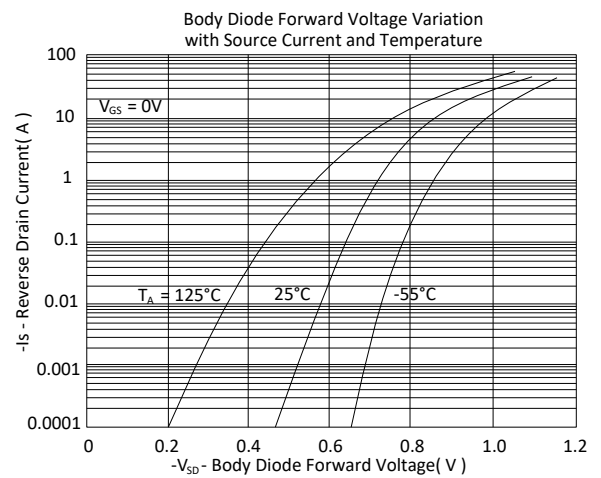
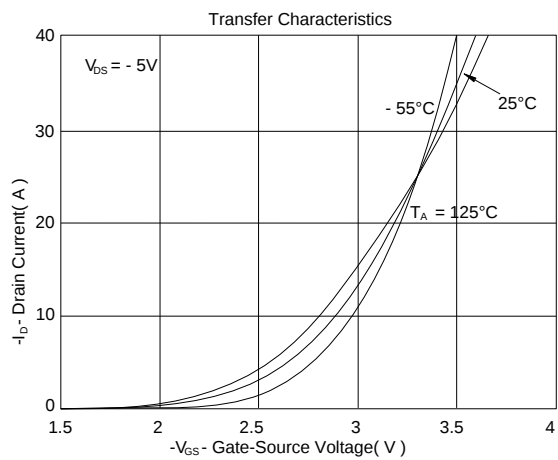
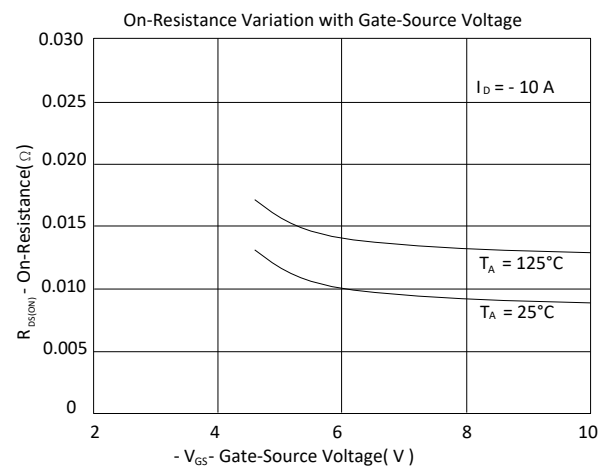
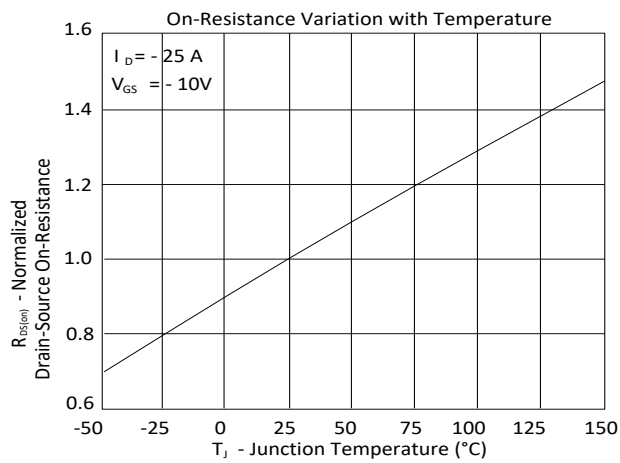
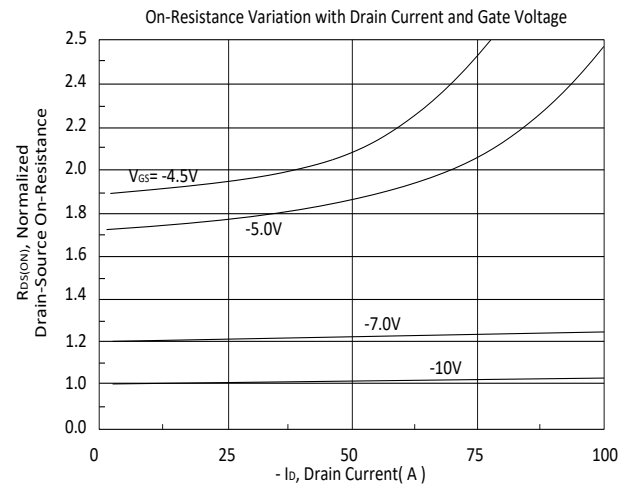
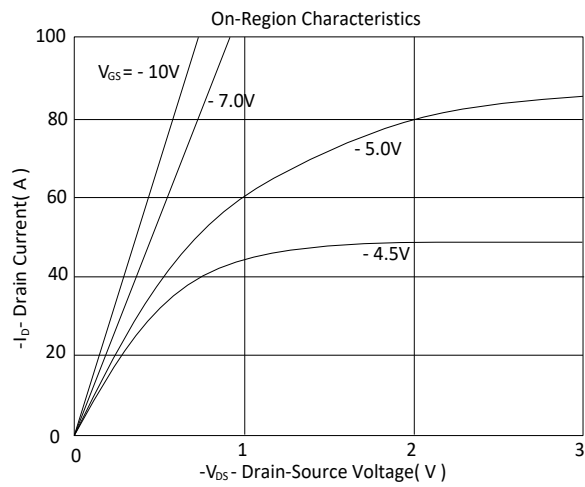


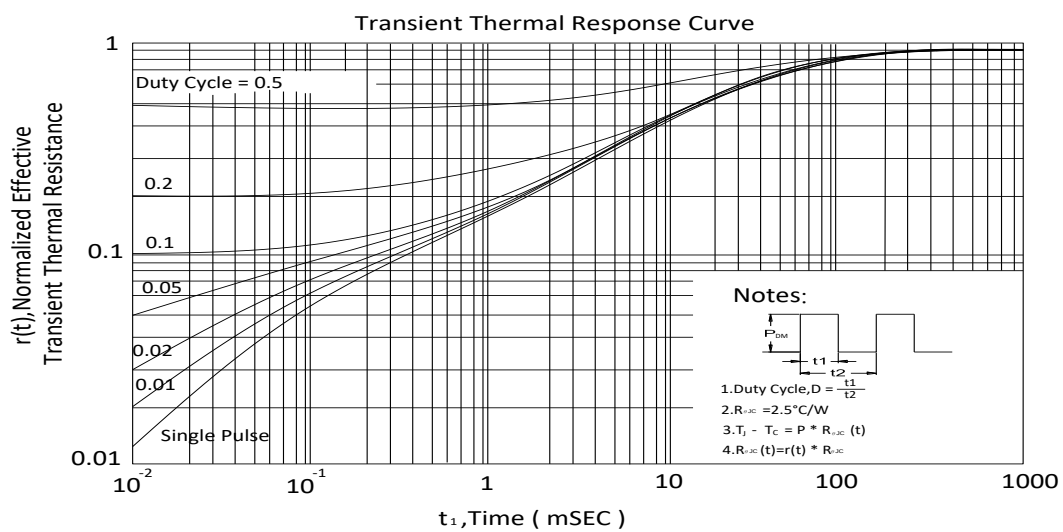
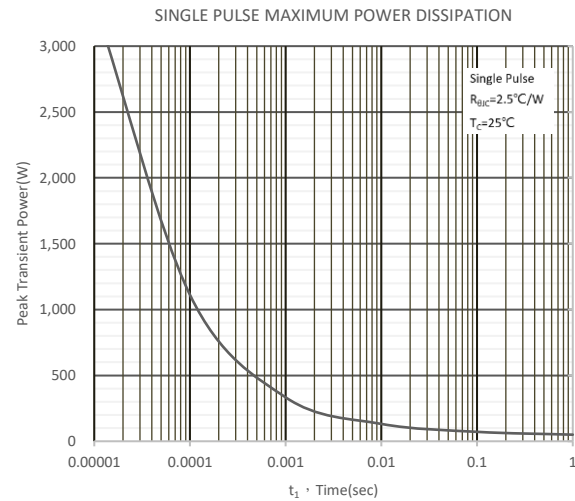
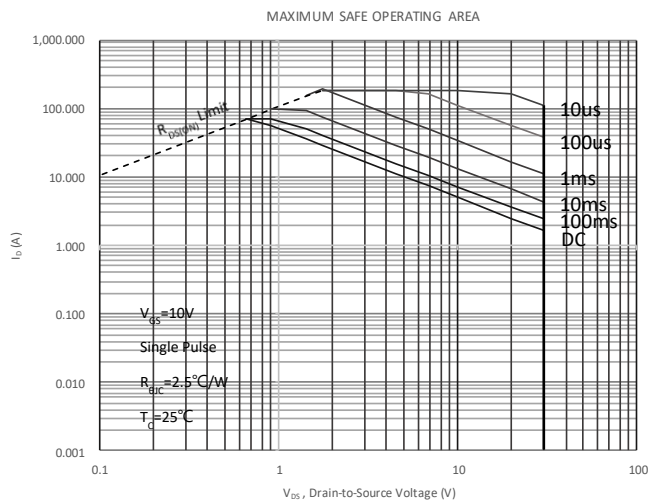
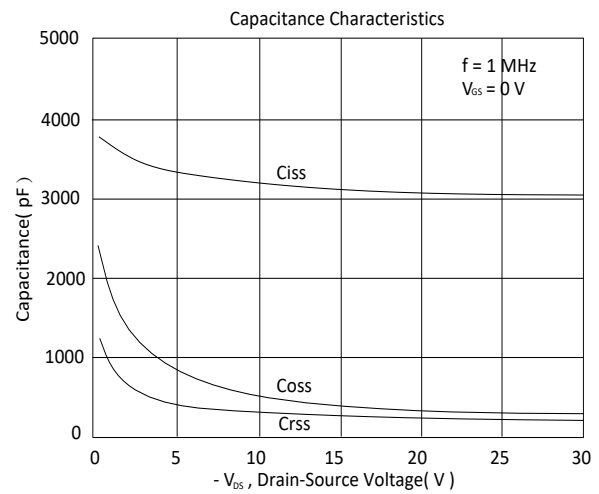
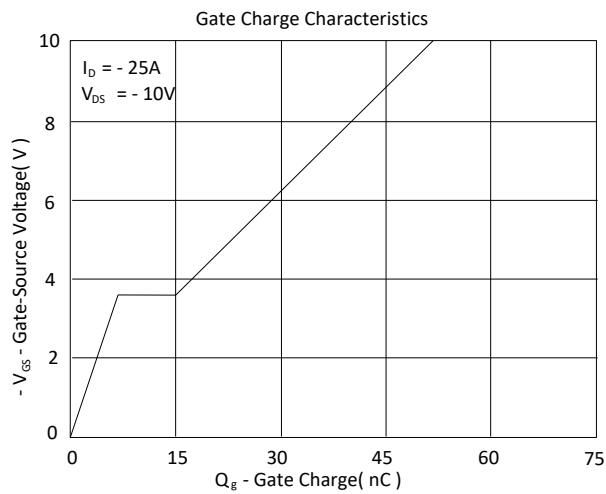
¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

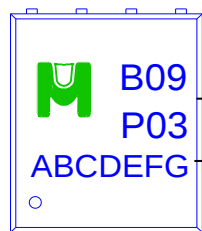
EMC will review datasheet by quarter, and update new version.





Ordering & Marking Information:

Device Name: EMB09P03H for EDFN 5 x 6



B09P03: Device Name

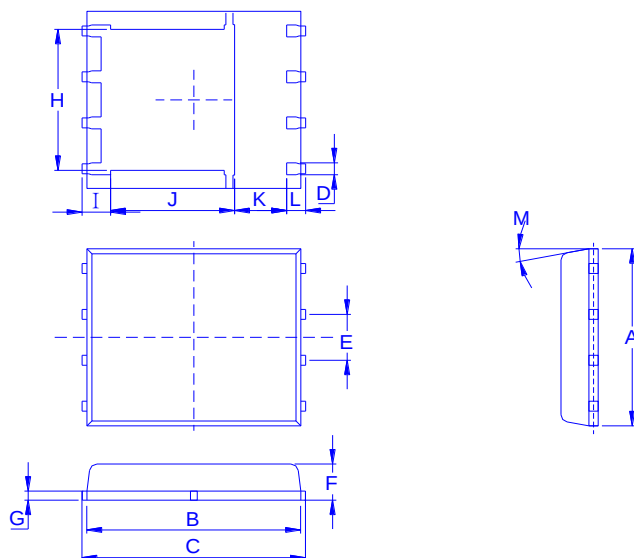
ABCDEFGH: Date Code

A: Assembly House

B: Year(A:2008 B:2009 C:2010....)

C: Month(A:01 B:02 C:03 D:04 E:05 F:06 G:07 H:08 I:09 J:10 K:11 L:12)

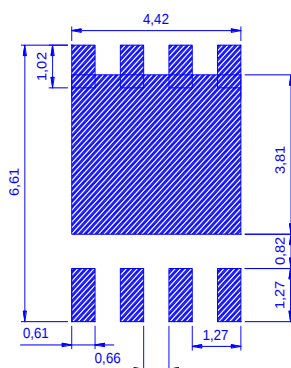
Outline Drawing



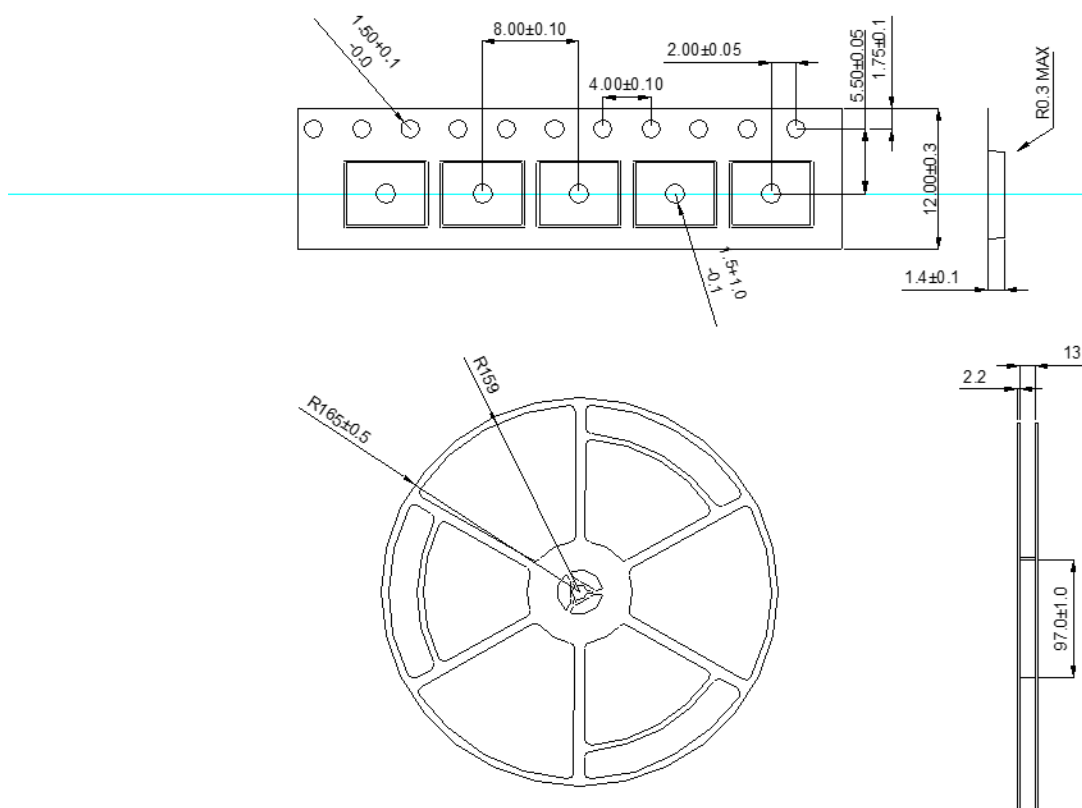
Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K	L	M
Min	4.8	5.55	5.9	0.3	1.17	0.85	0.15	3.61	0.38	3.18	1	0.38	0°
Typ.	4.9	5.7	6	0.4	1.27	0.95	0.2	3.87	0.4	3.44	1.195	0.4	
Max	5.4	5.85	6.15	0.51	1.37	1.17	0.34	4.31	0.711	3.78	1.39	0.71	12°

Footpoint



◆ Tape&Reel Information:2500pcs/Reel(Dimension in millimeter)



產品別	EDFN5X6
Reel 尺寸	13"
編帶方式	FEED DIRECTION
前空格	25
後空格	50
裝箱數	
滿捲數量	2.5K
捲/內盒比	01:01
內盒滿箱數	2.5K
內/外箱比	10:01
外箱滿箱數	25K